

# NPN SILICON RF POWER TRANSISTOR

**DESCRIPTION:**

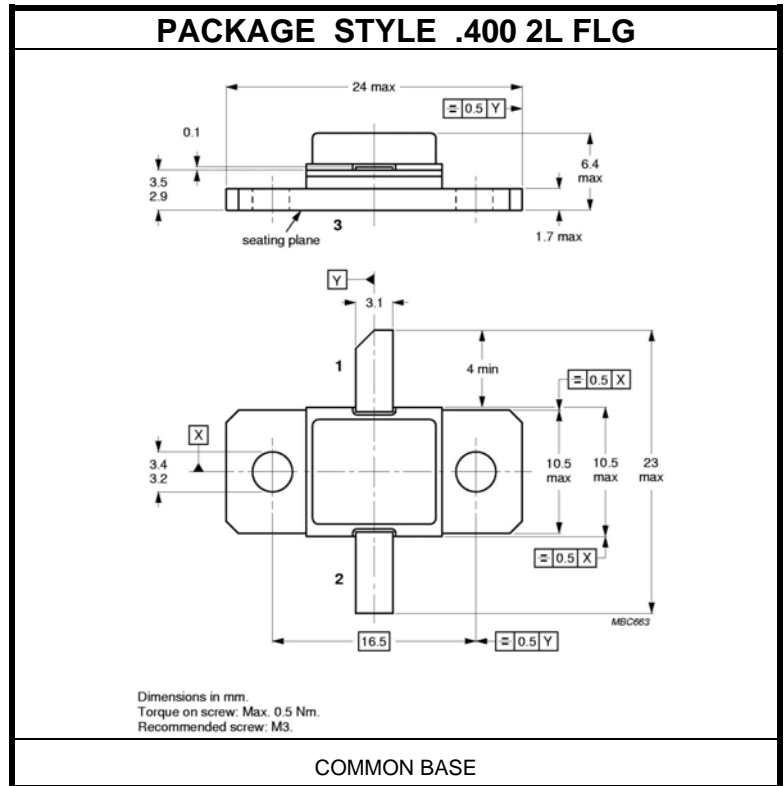
The **ASI RZ1214B65Y** is Designed for 1200 – 1400 MHz, L-Band Applications.

**FEATURES:**

- Internal Input/Output Matching Network
- $P_G = 7.0$  dB at 80 W/1400 MHz
- **Omnigold™** Metalization System

**MAXIMUM RATINGS**

$I_C$	6.0 A
$V_{CB}$	60 V
$P_{DISS}$	180 W @ $T_{mb} = 75$ °C
$T_J$	-65 °C to +200 °C
$T_{STG}$	-65 °C to +200 °C
$\theta_{JC}$	2.5 °K/W


**CHARACTERISTICS**  $T_C = 25$  °C

SYMBOL	TEST CONDITIONS		MINIMUM	TYPICAL	MAXIMUM	UNITS
$BV_{CBO}$	$I_C = 4.0$ mA		60			V
$BV_{CER}$	$I_C = 4.0$ mA	$R_{BE} = 10$ Ω	60			V
$BV_{EBO}$	$I_E = 400$ μA		3.0			V
$I_{CBO}$	$V_{CE} = 50$ V				2.0	mA
$h_{FE}$	$V_{CE} = 5.0$ V	$I_C = 2.0$ A	15		150	---
$P_G$	$V_{CC} = 50$ V	$P_{OUT} = 80$ W		7.0		dB
$\eta_C$		$f = 1.2$ to 1.4 GHz		38		%